



MICRON.173GEN

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MICRON.198A

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : MICRON TECHNOLOGY, INC.)
App. No. : listed below)
Filed : listed below)
For : listed below)
Examiner : Unknown)

ESTABLISHMENT OF RIGHT OF ASSIGNEE TO TAKE ACTION
AND
REVOCATION AND POWER OF ATTORNEY

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

The undersigned is empowered to act on behalf of the assignee below (the "Assignee") for the cases listed below. The original Assignment from Honeywell, Inc. to Micron Technology, Inc. is recorded at Reel 012188 and Frame 0697, and each of the listed cases was previously assigned of record to Honeywell, Inc.:

App. No.	Off/Reel No.	Title	Patent No.	Assignment Reel/Frame
09/318,073	MICRON.196CP1	Local Shielding For Memory Cells	PENDING	009993/0887
09/618,237	MICRON.211A	Magneto-Resistive Memory Array	PENDING	011267/0257
09/618,256	MICRON.210A	Magneto-Resistive Memory Having Sense Amplifier With Offset Control	PENDING	011430/0400
09/618,492	MICRON.212A	Memory Redundancy With Programmable Non-Volatile Control	PENDING	011377/0194
09/618,504	MICRON.198A	MRAM Architectures For Increased Write Selectivity	PENDING	012188/0697
09/638,415	MICRON.213A	Magneto-Resistive Memory With Shared Wordline And	PENDING	011189/0647

App. No. : listed below
 Filed : listed below

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App. No.	Office Ref. No.	Sense Line	Patent No.	Assignment Ref. No.
09/638,419	MICRON.214A	Passivated Magneto-Resistive Bit Structure And Passivation Method Therefor	PENDING	011287/0078
09/638,637	MICRON.215A	Pulsed Write Techniques For Magneto-Resistive Memories	PENDING	011262/0993
09/668,922	MICRON.216A	Shielding Arrangement To Protect A Circuit From Stray Magnetic Fields	PENDING	011199/0931
08/962,512	MICRON.197A	Shielded Package For Magnetic Devices	5,939,772	9147/0852
08/993,009	MICRON.196A	Self-Aligned Wordline Keeper And Method Of Manufacture Therefor	5,956,267	8940/0969
08/962,518	MICRON.208A	MRAM Design To Reduce Dissimilar Nearest Neighbor Effects	5,982,658	9066/0083
08/940,587	MICRON.207A	Method To Permit High Temperature Assembly Processes For Magnetically Sensitive Devices	6,027,948	N/A
08/993,005	MICRON.209A	Method Of Manufacturing A High Density Magnetic Memory Device	6,048,739	8940/0979
09/365,308	MICRON.206A	Method And Apparatus For Reading A Magneto-Resistive Memory	6,134,138	010147/0942
09/396,189	MICRON.185DV1	Non-Volatile Storage Latch	6,147,922	9115/0907
09/429,664	MICRON.185CP1	Non-Volatile Storage Latch	6,175,525	010353/0253
09/455,850	MICRON.199A	Method And Apparatus For Writing Data States To Non-Volatile Storage Devices	6,178,111	010477/0485
09/059,871	MICRON.185A	Non-Volatile Storage Latch	6,269,027	9115/0907
06/879,679	MICRON.189A	Magneto-Resistive Memory Including Thin Film Storage Cells Having Tapered Ends	4,731,757	4574/0767
06/908,075	MICRON.187A	Differential Arrangement Magnetic Memory Cell	4,751,677	4604/0016
07/008,211	MICRON.195A	Vialess Shorting Bars For Magneto-Resistive Devices	4,754,431	4664/0251
06/870,068	MICRON.188A	Magneto-Resistive Memory With Multi-Layer Storage Cells Having Layer Of Limited	4,780,848	4559/0920

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 Filed : listed below

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App. No.	Disc. Ref. No.	Thickness	Patent No.	Assignment Reel/Frame
07/078,612	MICRON.186A	Differential Magneto-Resistive Memory Sensing	4,829,476	4748/0535
07/168,293	MICRON.192DV1 MICRON.195DV1	Vialess Shorting Bars For Magneto-Resistive Devices	4,897,288	4664/0251
07/161,534	MICRON.194A	Magnetic Device Integrated Circuit Interconnection System	4,918,655	4838/0775
07/404,003	MICRON.203FW1	Semiconductor Device Housing With Magnetic Field Protection	4,953,002	4896/0504
07/504,777	MICRON.191A	Opposed Field Magneto- Resistive Memory Sensing	5,012,444	5269/0357
07/505,090	MICRON.190A	Magnetic State Entry Assurance	5,060,193	5275/0230
07/507,682	MICRON.193A	Inductively Sensed Magnetic Memory	5,064,499	5283/0794
08/061,603	MICRON.202A	Sense Amplifier Input Stage For Single Array Memory	5,349,302	6564/0073
08/365,852	MICRON.204A	Highly Produable Magneto- Resistive RAM Process	5,496,759	7300/0805
08/576,279	MICRON.205A	Integrated Spacer For Magneto- Resistive RAM	5,569,617	7822/0914
08/576,732	MICRON.200A	Magnetic Hardening Of Bit Edges Of Magneto-Resistive RAM	5,756,366	7807/0166

The original assignment from Honeywell, Inc. to Micron Technology, Inc. is recorded at Reel 012188 and Frame 0697. These assignments represents the entire chain of title of these inventions from the Inventors to the Assignee.

I declare that all statements made herein are true, and that all statements made upon information and belief are believed to be true, and further, that these statements were made with the knowledge that willful, false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. § 1001, and that willful, false statements may jeopardize the validity of the application, or any patent issuing thereon.

The undersigned hereby revokes any previous powers of attorney in the subject application, and hereby appoints the registrants of Knobbe, Martens, Olson & Bear, LLP, 620 Newport Center Drive, Sixteenth Floor, Newport Beach, California 92660, Telephone (949) 760-0404, Customer No. 20,995, and Michael L. Lynch, Reg. No. 30,871, Micron Technology, Inc., 8000 South Federal Way, P.O. Box 6, Boise, ID 83707-0006, as its attorneys

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with full power of substitution and revocation to prosecute this application and to transact all business in the U.S. Patent and Trademark Office connected herewith. This appointment is to be to the exclusion of the inventor(s) and his attorney(s) in accordance with the provisions of 37 C.F.R. § 3.71.

Please use Customer No. 20,995 for all communications.

MICRON TECHNOLOGY, INC.

Dated: February 28, 2002

By: Roderic Lewis
Roderic Lewis

Vice President of Legal Affairs,
Title: General Counsel and Corporate Secretary

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